IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Application of: Wolfgang M.J. Hofmann and Noel C. MacDonald]
Application No. Division of 10/021,311)) Group:
Filed: Even date herewith) Examiner:
For: MULTIPLE-LEVEL ACTUATORS AND CLAMPING DEVICES))

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 CFR 1.97 and 1.98, applicant hereby makes of record the documents listed on the attached PTO form 1449. A copy of each document may be found in copending parent application No. 10/021,311, pending in Group Art Unit 1772, with the exception of the newlycited article entitled "Deep Silicon RIE with Profile Control" dated October 23, 1997.

Very truly yours,

JONES, TULLAR & COOPER, P.C.

George M. Cooper Registration No. 20,201

JONES, TULLAR & COOPER, P.C. P.O. Box 2266 Eads Station Arlington, VA 22202 (703) 415-1500 October 7, 2003

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STATEMENT BY APPLICANT			First Named Inventor	Wolfgang M.J. Hofmann			
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Sheet	1	of 1	Attorney Docket Number	Hofmann	j		

-			U.S. PATENT DOC	UMENTS	
Examiner nitials*	Cite No.1	U.S. Patent Docum Kind C (if knc	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		5,198,390	MacDonald	03/03/1993	
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				U.S. PATENT DOC	UMENTS	
Examiner Cite		U.S. Patent	Document Kind Code ²	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant
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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	_
xaminer nitials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		CHANG, T.H.P.k Kern, D.P., Muray, L.P.; Microminiaturization of electron optical systems; J. Vacuum Science & Technology B, vol. 8, pp. 1698-1705, 1990	
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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	
Examiner nitials	Cite No. ¹	item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	1
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